

**DRAFT - FOR EXAMINER REVIEW ONLY
NOT FOR FILING**

Attorney Docket No. YAO-3950US2
PATENT

In re Application of
Yoshihisa Nagano et al.

: Group Art Unit: 2815
: Examiner: Jose R. Diaz

Serial No.: 10/170,168

Filed: June 12, 2002

For: SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

AMENDMENT UNDER 37 C.F.R. § 1.111

IN THE CLAIMS:

Please amend claims 28 and add new claim 47 as follows.

1. (Currently amended) A method for fabricating a semiconductor device,
comprising the step of:

sequentially forming a lower electrode, a dielectric film comprising ~~either~~
~~dielectric material having a high dielectric constant or~~ a ferroelectric ~~[material]~~ film, and
an upper electrode on a supporting substrate ~~[having an integrated]~~, thereby forming a
capacitor;

forming a first interlayer insulating film provided so as to cover the capacitor;

forming a first contact hole in the first interlayer insulating film;